



TS820-B/T

SENSITIVE SCR

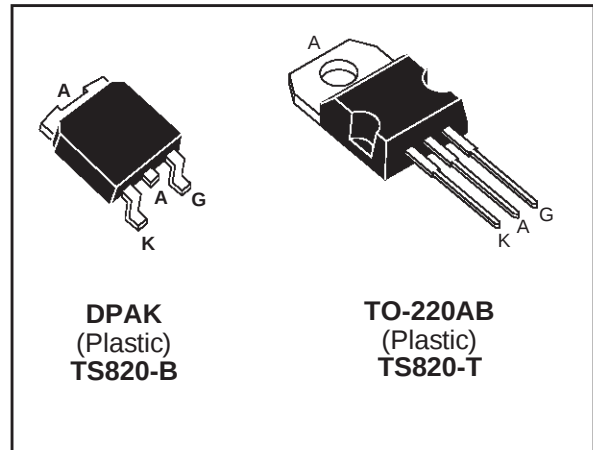
FEATURES

- $I_{T(RMS)} = 8A$
- $V_{DRM}/V_{RRM} = 400, 600V, 700V$
- $I_{GT} < 200\mu A$
- SMD PACKAGE

DESCRIPTION

The TS820-B/T series of SCR use a high performance TOPGLASS PNPN technology.

The parts are intended for general purpose applications using surface mount or through hole technology.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$I_{T(RMS)}$	RMS on-state current (180° conduction angle)	$T_c = 110^{\circ}C$	8	A
$I_{T(AV)}$	Average on-state current (180° conduction angle)	$T_c = 110^{\circ}C$	5	A
I_{TSM}	Non repetitive surge peak on-state current (T_j initial = 25°C)	$t_p = 8.3ms$ $t_p = 10ms$	73 70	A
I^2t	I^2t Value for fusing	$t_p = 10ms$	24	A ² s
dI/dt	Critical rate of rise of on-state current $I_G = 10 mA$ $dI_G/dt = 0.1 A/\mu s$.		100	A/ μs
T_{stg} T_j	Storage junction temperature range Operating junction temperature range		- 40 to + 150 - 40 to + 125	°C
TI	Maximum temperature for soldering during 10s		260	°C

Symbol	Parameter	TS820-			Unit
		400B/T	600B/T	700B/T	
V_{DRM}	Repetitive peak off-state voltage	400	600	700	V
V_{RRM}	$T_j = 125^{\circ}C$ $R_{GK} = 220 \Omega$				

TS820-B/T

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth(j-a)	Junction to ambient ($S=0.5\text{cm}^2$)	DPAK	70	°C/W
		TO-220AB	60	
Rth(j-c)	Junction to case for DC	DPAK / TO-220AB	2.0	°C/W

GATE CHARACTERISTICS (maximum values)

P_G (AV) = 0.2 W P_{GM} = 3 W (t_p = 20 μ s) I_{GM} = 1.2 A (t_p = 20 μ s)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Type	Value	Unit
I_{GT}	$V_D=12\text{V}$ (DC) $R_L=140\Omega$	$T_j=25^\circ\text{C}$	MAX	200	μA
V_{GT}	$V_D=12\text{V}$ (DC) $R_L=140\Omega$	$T_j=25^\circ\text{C}$	MAX	0.8	V
V_{GD}	$V_D=V_{DRM}$ $R_L=3.3\text{k}\Omega$ $R_{GK}=220\Omega$	$T_j=125^\circ\text{C}$	MIN	0.1	V
V_{RG}	$I_{RG}=10\mu\text{A}$	$T_j=25^\circ\text{C}$	MIN	8	V
I_H	$I_T=50\text{mA}$ $R_{GK}=1\text{K}\Omega$	$T_j=25^\circ\text{C}$	MAX	5	mA
V_{TM}	$I_{TM}=16\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^\circ\text{C}$	MAX	1.6	V
I_{DRM}	$V_D=V_{DRM}$ $R_{GK}=220\Omega$	$T_j=25^\circ\text{C}$	MAX	5	μA
I_{RRM}	$V_R=V_{RRM}$ $R_{GK}=220\Omega$	$T_j=125^\circ\text{C}$	MAX	1	mA
dV/dt	$V_D=67\%V_{DRM}$ $R_{GK}=220\Omega$	$T_j=125^\circ\text{C}$	MIN	5	V/ μs

ORDERING INFORMATION Add "-TR" suffix for Tape & Reel shipment

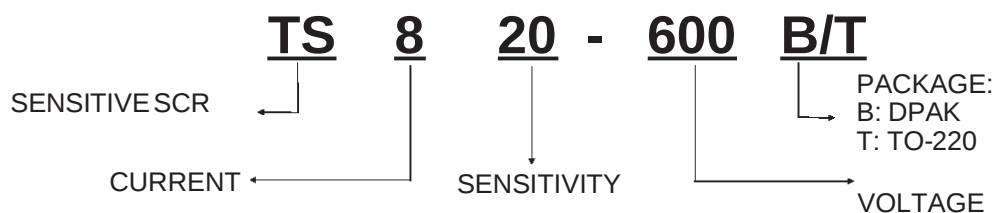


Fig. 1: Maximum average power dissipation versus average on-state current.

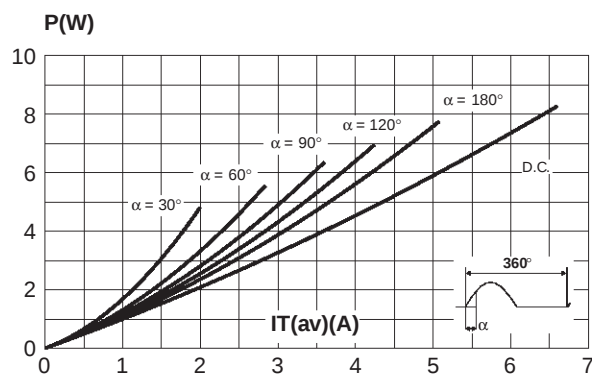


Fig. 2: Correlation between maximum average power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact.

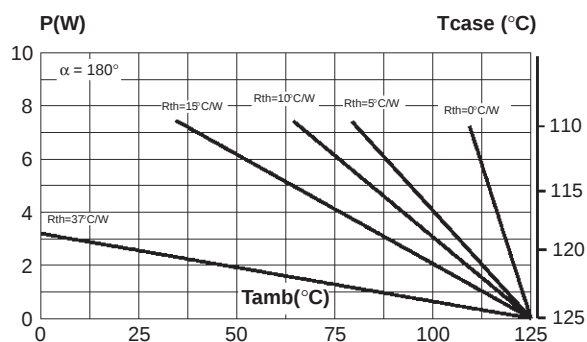


Fig. 3-1: Average and D.C. on-state current versus case temperature (TO-220AB).

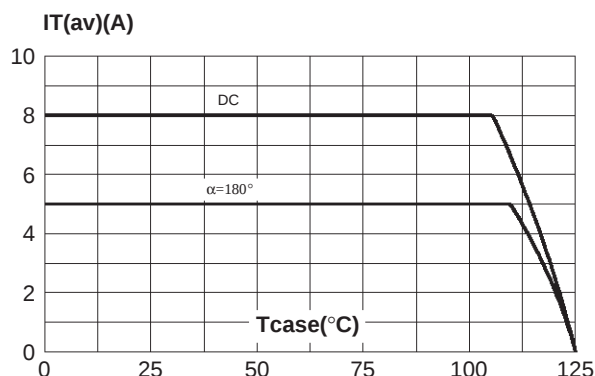


Fig. 3-2: Average and D.C. on-state current versus ambient temperature (device mounted on FR4 with recommended pad layout) (DPAK).

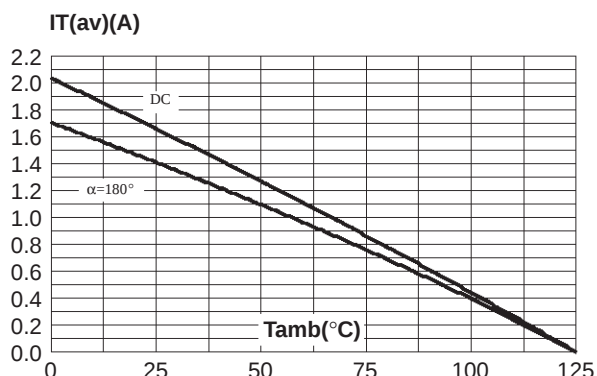


Fig. 4-1: Relative variation of thermal impedance junction to case versus pulse duration.

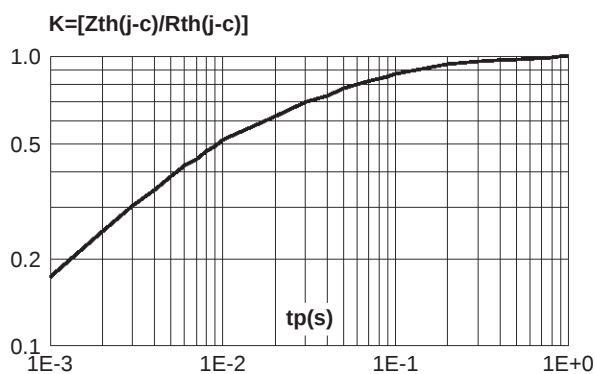


Fig. 4-5: Relative variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, FR4 PC board) (DPAK).

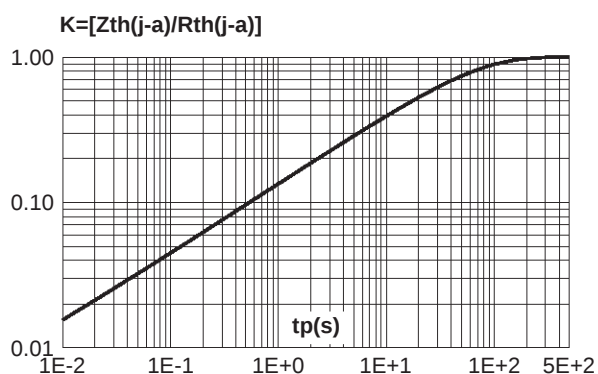


Fig. 5: Relative variation of gate trigger current and holding current versus junction temperature.

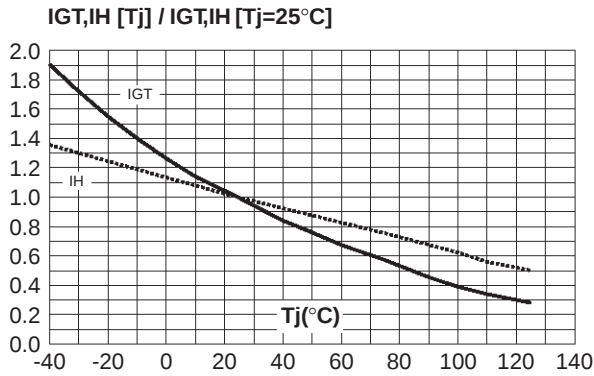


Fig. 7: Non repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$, and corresponding value of $I^2 t$.

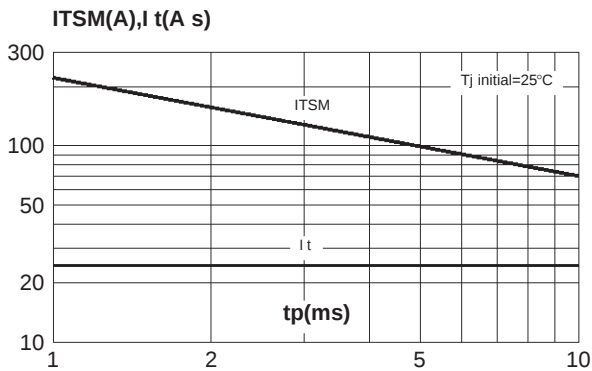


Fig. 9: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness: $35\mu\text{m}$) (DPAK).

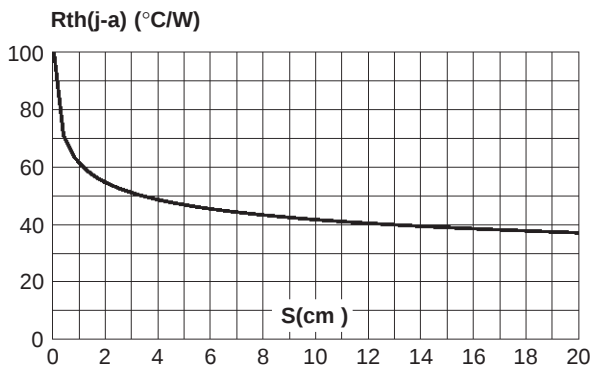


Fig. 6: Non repetitive surge peak on-state current versus number of cycles.

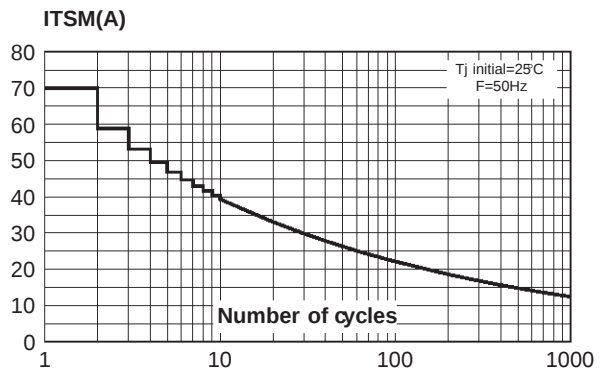


Fig. 8: On-state characteristics (maximum values).

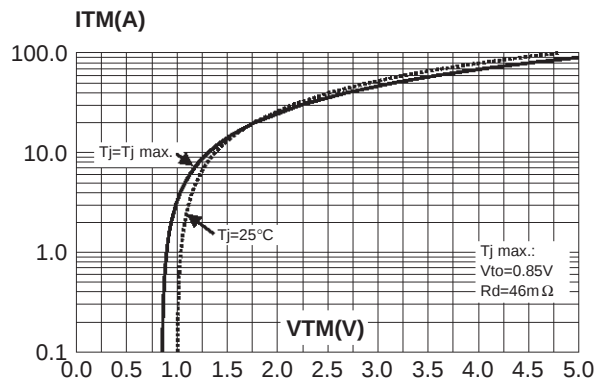
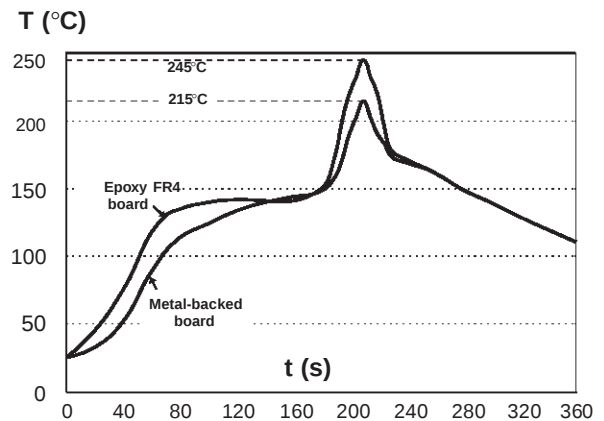
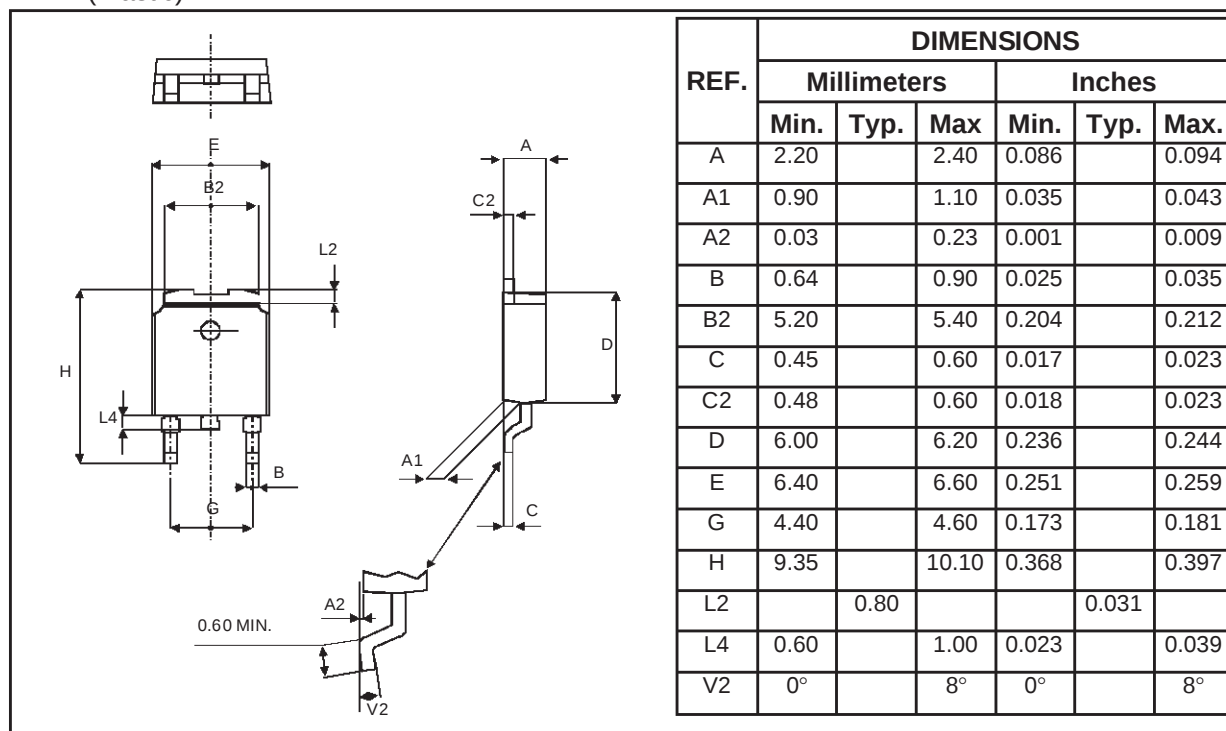
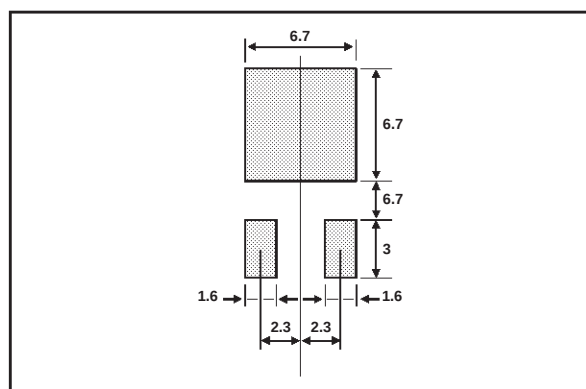


Fig. 10: Typical reflow soldering heat profile, either for mounting on FR4 or metal-backed boards.



PACKAGE MECHANICAL DATA
 DPAK (Plastic)

FOOT PRINT DIMENSIONS (in millimeters)


TS820-B/T

PACKAGE MECHANICAL DATA

TO-220AB(Plastic)

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

Type	Marking	Package	Weight	Base qty	Delivery mode
TS820-B	TS820x00B	DPAK	0.3 g.	75	Tube
				2500	Tape and Reel
TS820-T	TS820x00T	TO-220AB	2 g.	50	Tube

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